

CLAIMS

1. A pn junction type Group III nitride semiconductor light-emitting device having a light-emitting layer of multiple quantum well structure in which well layers and barrier layers including Group III nitride semiconductors are alternately stacked periodically between an n-type clad layer and a p-type clad layer which are formed on a crystal substrate and which include Group III nitride semiconductors,
5 Wherein one end layer of the light-emitting layer is closest to and opposed to the n-type clad layer, and the other end layer of the light-emitting layer is closest to and opposed to the p-type clad layer, both the one and the other end layers are barrier layers, and the other end layer is thicker than
10 the barrier layer of the one end layer.
2. The pn junction type Group III nitride semiconductor light-emitting device according to claim 1, wherein each of the barrier layers has a thickness increased gradually from
20 the one end layer toward the other end layer.
3. The pn junction type GROUP III nitride semiconductor light-emitting device according to claim 1 or 2, wherein the other end layer has an impurity concentration low at its junction
25 portion relative to the well layer, highest at its central portion and reduced gradually from the central portion toward the p-type clad layer.
4. The pn junction type GROUP III nitride semiconductor light-emitting device according to any one of claims 1 to 3,
30 wherein the other end layer has joined thereto a well layer which is not intentionally doped with impurities.